

Date:- 14th Dec, 2009

Data Sheet Issue:- 1

Provisional Data

Rectifier Diode

Types W3082MC420 to W3082MC450

Old part number Wx253MC420-450

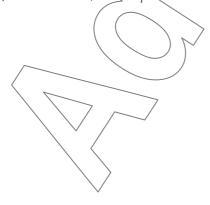
Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{RRM}	Repetitive peak reverse voltage, (note 1)	4200-4500	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)	4300-4600	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
$I_{F(AV)M}$	Maximum average forward current, T _{sink} =55°C, (note 2)	3120	А
$I_{F(AV)M}$	Maximum average forward current. T _{sink} =100°C (note 2)	2185	Α
$I_{F(AV)M}$	Maximum average forward current. T _{sink} =100°C, (note 3)	1308	Α
I _{F(RMS)M}	Nominal RMS forward current, T _{sink} =25°C, (note 2)	5716	Α
I _{F(d.c.)}	D.C. forward current, T _{sink} =25°C, (note 4)	5080	А
I _{FSM}	Peak non-repetitive surge t _p =10ms, V _m =60%V _{RRM} (note 5)	26.0	kA
I _{FSM2}	Peak non-repetitive surge t _p =10ms/V _m ≤10V, (note 5)	28.6	kA
l ² t	I^2 t capacity for fusing $t_p=10$ ms, $V_{rm}=60\%V_{RRM}$ (note 5)	3.38×10 ⁶	A ² s
l ² t	I ² t capacity for fusing t _p =10ms, V _{rm} ≤10V, (note 5)	4.09×10 ⁶	A ² s
T _{j op}	Operating temperature range	-40 to +160	°C
T_{stg}	Storage temperature range	-55 to +160	°C

Notes:

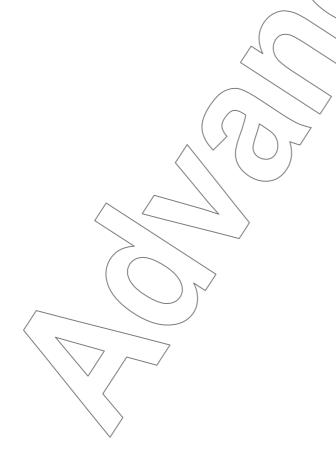
- 1) De-rating factor of 0.13% per °C is applicable for T_i below 25°C.
- 2) Double side cooled, single phase, 50Hz, 180° half-sinewave.
- 3) Cathode side cooled, single phase; 50Hz, 180° half-sinewave.
- 4) Double side cooled.
- 5) Half-sinewave, 160°C T_i initial.



Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V_{FM}	Maximum peak forward voltage	-	-	1.50	I _{FM} =3000A	V
V_{FM}	Maximum peak forward voltage	-	-	2.58	I _{FM} =8600A	V
V_{T0}	Threshold voltage	-	-	0.923		V
r _T	Slope resistance	-	-	0.192		mΩ
I _{RRM}	Peak reverse current	-	-	50	Rated V _{RRM}	mA
Q_{rr}	Recovered charge	-	6800	7800	(0)	μC
Q_{ra}	Recovered charge, 50% Chord	-	4300	- /	I _{TM} =2000A, t _p =1000μs, di/dt=10A/μs,	μC
I _{rm}	Reverse recovery current	-	190	_	√ _r =100V	Α
t _{rr}	Reverse recovery time, 50% chord	-	45	-		μs
		-	-	0.0140	Double side cooled	K/W
R_{thJK}	Thermal resistance, junction to heatsink	-	-	0.0265	Anode side cooled	K/W
		-	-	0.0297	Cathode side cooled	K/W
F	Mounting force	25	- /	31	Note 2	kN
W_t	Weight		270 (<i>Y</i> < \	g

- Unless otherwise indicated T_j=160°C.
 For other clamp forces, please consult factory.



Notes on Ratings and Characteristics

1.0 Voltage Grade Table

Voltage Grade	V _{RRM} V	V _{RSM} V	V _R D¢ V
42	4200	4300	2820
44	4400	4500	2950
45	4500	4600	3020

2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for T₁ below 25°C.

4.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

5.0 Computer Modelling Parameters

5.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_{T0} + \sqrt{{V_{T0}}^2 + 4 \cdot ff^2 \cdot r_T \cdot W_{AV}}}{2 \cdot ff^2 \cdot r_T} \qquad \text{and:}$$

$$W_{AV} = \frac{\Delta T}{R_{th}}$$
 $\Delta T = T_{j \max} - T_{K}$

Where V_{T0} =0.923V, r_T =0.192m Ω , \angle

 $R_{\it th}$ = Supplementary thermal impedance, see table below and

ff = Form factor, see table below

Supplementary Thermal Impedance					
Conduction Angle	6 phase (60°)	3 phase (120°)	½ wave (180°)	d.c.	
Square wave Double Side Cooled	0.01665	0.01581	0.01516	0.0140	
Square wave/Cathode Side Cooled	0.03217	0.03147	0.03090	0.0297	
Sine wave Double Side Cooled	0.01612	0.01531	0.01436		
Sine wave Cathode Side Cooled	0.03174	0.03105	0.03022		
		•			

Form Factors				
Conduction Angle	6 phase (60°)	3 phase (120°)	½ wave (180°)	d.c.
Square waye	2.449	1.732	1.414	1
Sine wave	2.778	1.879	1.57	

5.2 Calculating V_F using ABCD Coefficients

The on-state characteristic I_F vs. V_F, on page 6 is represented in two ways;

- (i) the well established V_{T0} and r_T tangent used for rating purposes and
- (ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for V_F/in terms of I_F given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for V_F agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		160°C Coefficients		
Α	0.7209071	Α	0.4296331	
В	0.01368014	В	0.02648894	
С	9.201748 ×10 ⁻⁵	C	1.328307 ×10 ⁻⁴	
D	5.885724 ×10 ⁻³	6 /	8.312046 ×10 ⁻³	

5.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{\frac{-t}{\tau_p}}\right)$$

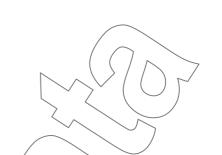
Where p = 1 to n, n is the number of terms in the series and:

t = Duration of heating pulse in seconds.

 r_{\downarrow} = Thermal resistance at time t.

 $\begin{array}{ll} r_p = & \text{Amplitude of } p_{th} \text{ term.} \\ \tau_p = & \text{Time Constant of } r_{th} \text{ term.} \end{array}$

The coefficients for this device are shown in the tables below:



Term	1	2	3	4
r_p	8.594785×10 ⁻³	3.308247×10 ⁻³	1.039072×10 ⁻³	7.916582×10 ⁻⁴
$ au_p$	0.7185764	0.09970181	0.02165834	5.266433×10 ⁻³

Term	1	2()//	3
r_p	0.02196926	5.845724×10 ^{/3}	1.904897×10 ⁻³
$ au_{p}$	4.127141	0.1629998	8.832583×10 ⁻³

6.0 Reverse recovery ratings

(i) Q_{ra} is based on 50% I_{rm} chord as shown in Fig.

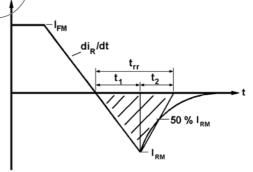
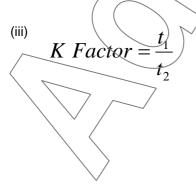
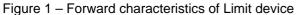


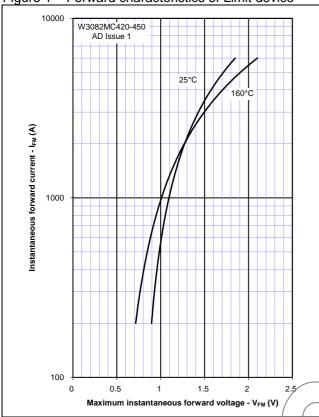
Fig. 1

$$Q_{rr} = \int_{0}^{150\,\mu s} i_{rr}.dt$$



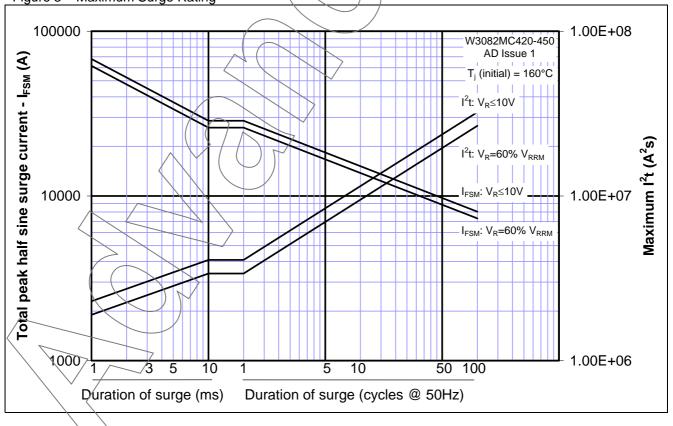
Curves

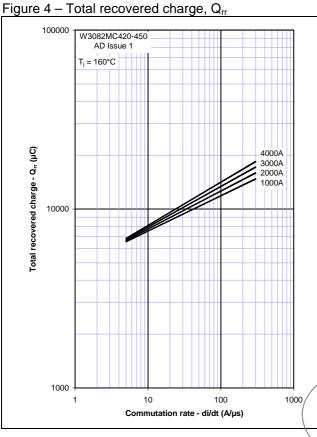


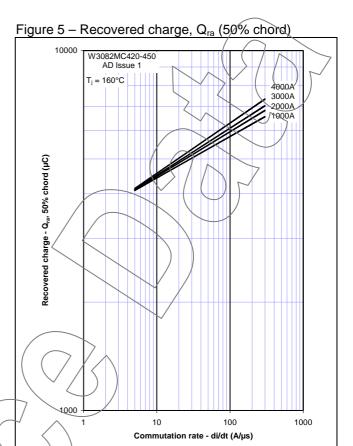


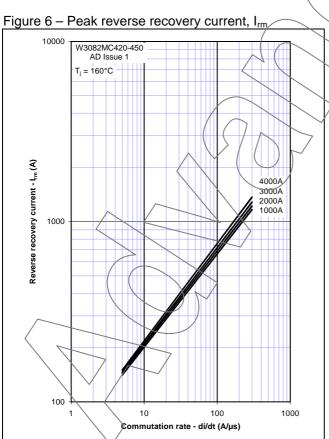
Time (s)

Figure 3 - Maximum Surge Rating









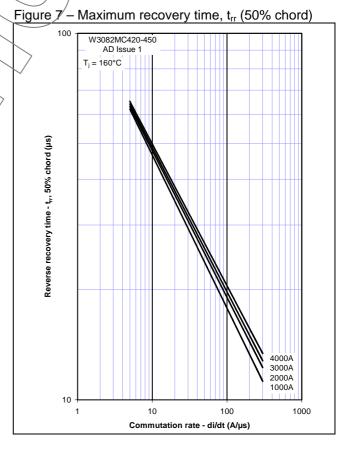


Figure 8 – Forward current vs. Power dissipation – Double Side Cooled

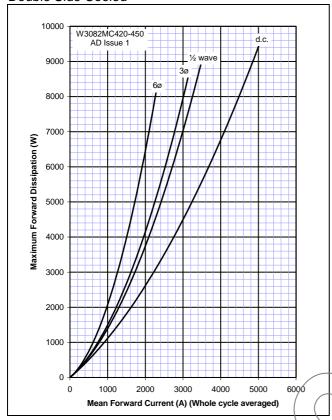


Figure 10 – Forward current vs. Power dissipation –

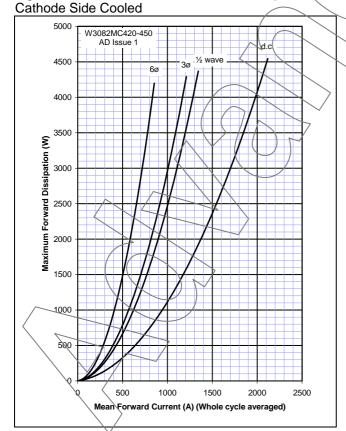
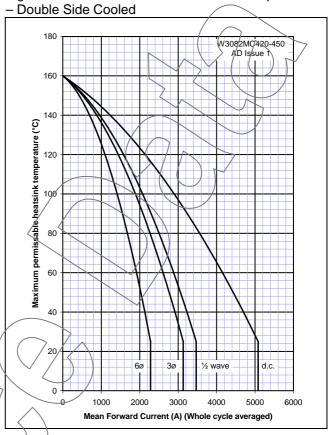
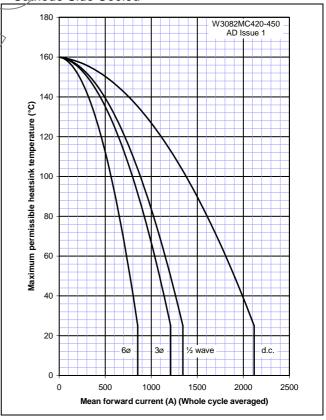


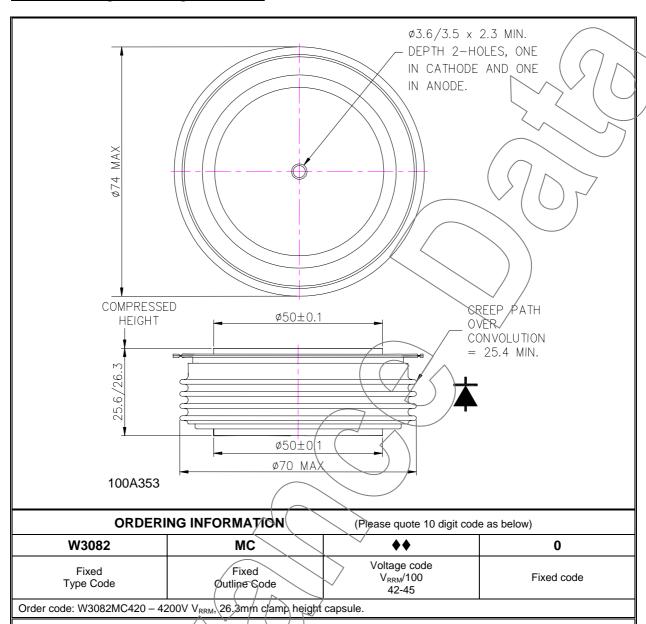
Figure 9 – Forward current vs. Heatsink temperature



Figure/11 – Forward current vs. Heatsink temperature – Cathode Side Cooled



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